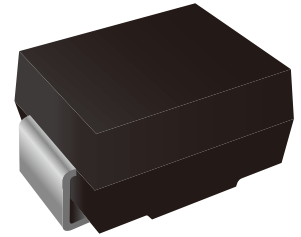


Thyristor Surge Suppressors (TSS) Data Sheet

Description

DO-214AA Thyristor solid state protection thyristor protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

The LTPB030B device is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, and TIA-968 (formerly known as FCC Part 68).



Features

Compared to surge suppression using other technologies, The LTPB030B device offers absolute surge protection regardless of the surge current available and the rate of applied voltage (dv/dt). The LTP030B device:

- Cannot be damaged by voltage
- Eliminate hysteresis and heat dissipation typically found with clamping devices
- Eliminate voltage overshoot caused by fast-rising transients
- Are non-degenerative
- Will not fatigue
- Have low capacitance, making them ideal for high-speed transmission equipment
- Meets MSL level 1, per J-STD-020

Thermal Considerations

Parameter	Symbol	Value	Unit
Operating Junction Temperature	T_J	-40 to +150	°C
Storage Temperature Range	T_S	-40 to +150	°C
Junction to Ambient on printed circuit	$R_{\theta JA}$	90	°C/W

Electrical Parameters

Parameter	Definition
V_{DRM}	Peak Off-state Voltage – maximum voltage that can be applied while maintaining off state
V_S	Switching Voltage – maximum voltage prior to switching to on state
V_T	On-state Voltage – maximum voltage measured at rated on-state current
I_{DRM}	Leakage Current – maximum peak off-state current measured at V_{DRM}
I_S	Switching Current – maximum current required to switch to on state
I_T	On-state Current – maximum rated continuous on-state current
I_H	Holding Current – typical current required to maintain on state
C_O	Off-state Capacitance – typical capacitance measured in off state
I_{PP}	Peak Pulse Current – maximum rated peak impulse current
I_{TSM}	Peak One-cycle Surge Current – maximum rated one-cycle AC current
di/dt	Rate of Rise of Current – maximum rated value of the acceptable rate of rise in current over time

Part Number	V_{DRM} (V)	V_S (V)	V_T (V)	I_{DRM} (μ A)	I_S (mA)	I_T (A)	I_H (mA)	C_O (pF)	Marking
LTPB030B	25	40	4	5	800	2.2	50	65	P030B

Notes:

- All measurements are made at an ambient temperature of 25°C. I_{PP} applies to -40°C through +85°C temperature range.
- Off-state capacitance(C_O) is measured at 1 MHz with a 2V bias and is typical value.

Surge Ratings

I_{PP} 2×10 μ s (A)	I_{PP} 8×20 μ s (A)	I_{PP} 10×160 μ s (A)	I_{PP} 10×560 μ s (A)	I_{PP} 10×1000 μ s (A)	I_{TSM} 60Hz (A)	di/dt (A/ μ s)
250	250	150	100	80	30	500

Ratings and Characteristics Curves

Figure 1. V-I Characteristics

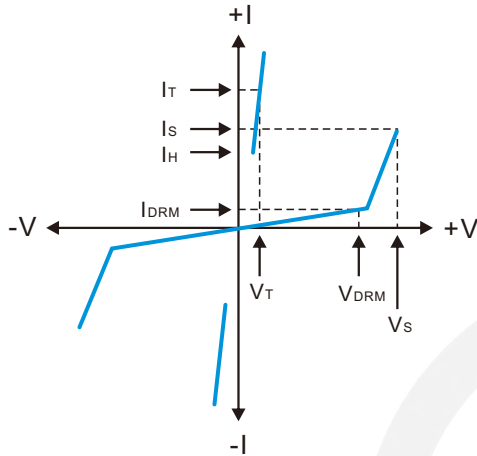


Figure 2. $t_r \times t_d$ Pulse Wave-form

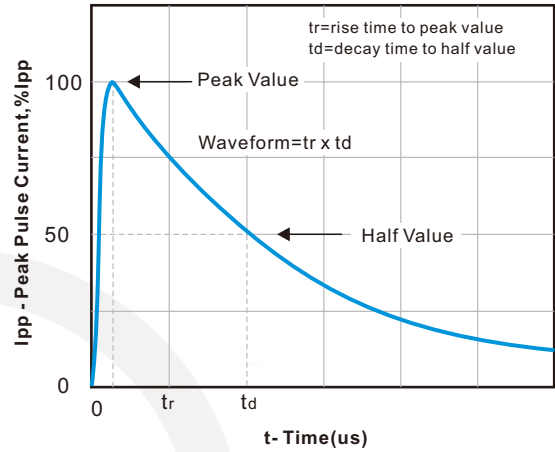


Figure 3. Normalized V_S Change versus Junction Temperature

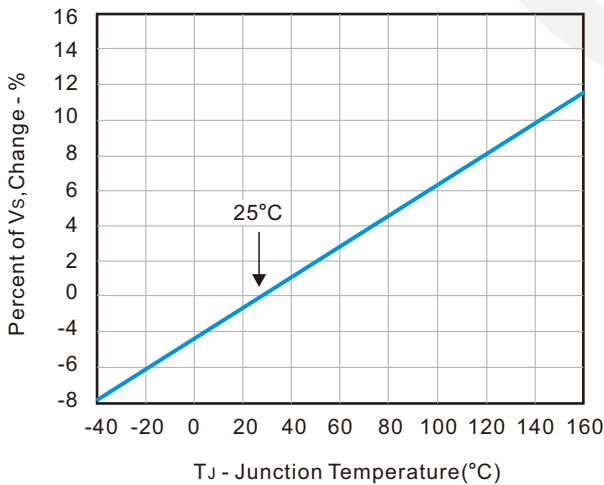
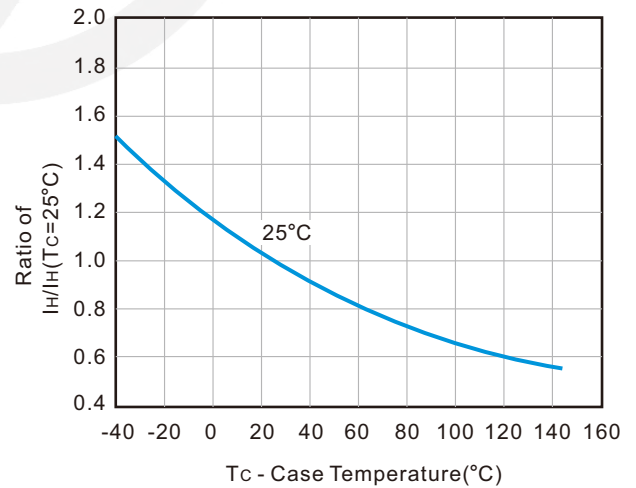
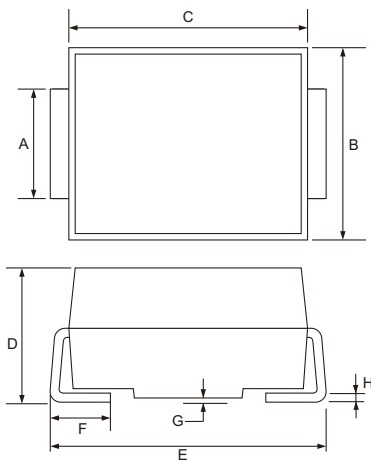


Figure 4. Normalized DC Holding Current versus Case Temperature



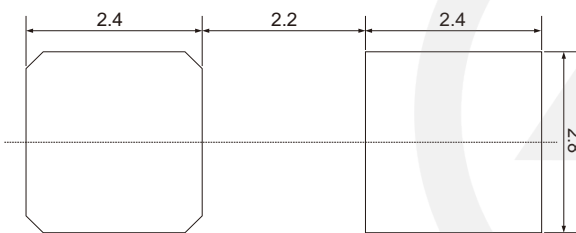
SMB Package Outline



Unit: mm

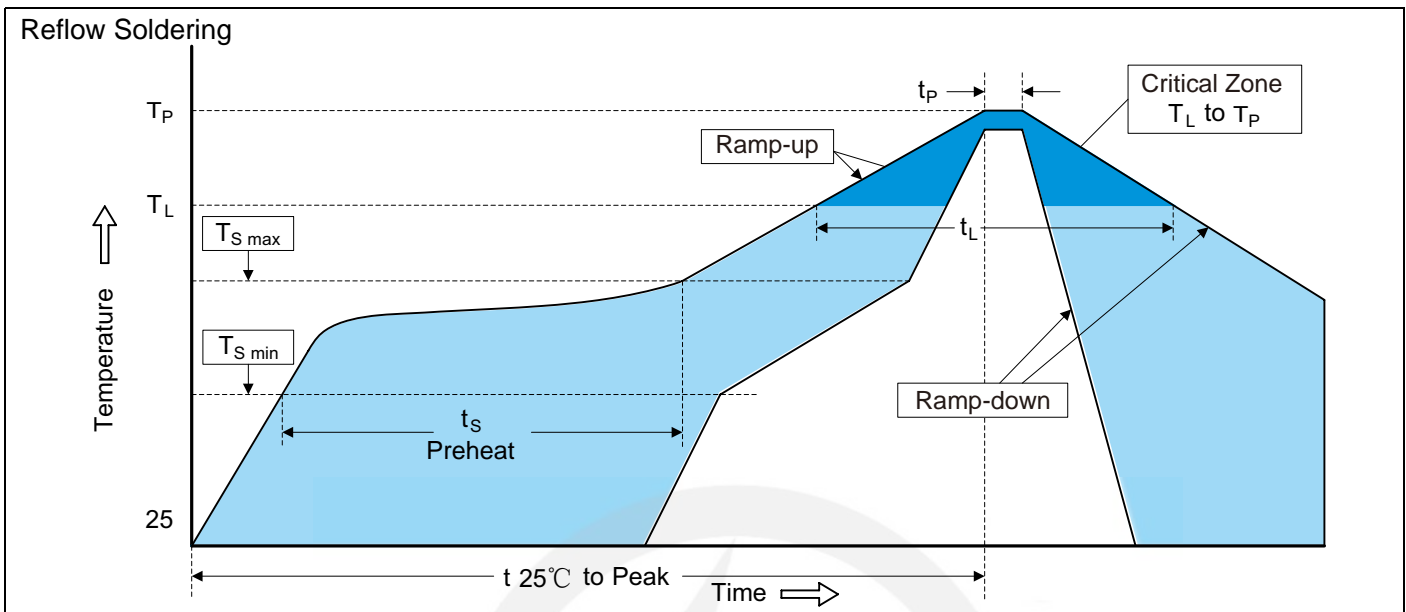
SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	1.90	2.20
B	3.30	3.94
C	4.05	4.75
D	2.13	2.65
E	5.08	5.59
F	0.76	1.52
G	0.203 TYP.	
H	0.15	0.31

SMB Suggested Pad Layout



Note:

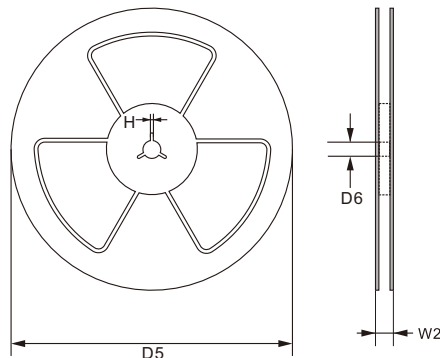
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purpose only.

Recommended Soldering Conditions

Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat -Temperature Min ($T_{S\ min}$) -Temperature Max ($T_{S\ max}$) -Time (min to max) (t_s)	150°C 200°C 60-180 seconds
$T_{S\ max}$ to T_L -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature (T_L) -Time (t_L)	217°C 60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_P)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Packaging

13" Reel


 D5 $\Phi 330.0 \pm 2.0$

 D6 $\Phi 13.5 \pm 0.5$

 H 2.5 ± 1.0

 W2 16.0 ± 2.0

Quantity: 3000PCS